

Title (en)

METHOD FOR MAKING CONTACT WITH A SEMICONDUCTOR AND CONTACT ARRANGEMENT FOR A SEMICONDUCTOR

Title (de)

VERFAHREN ZUM KONTAKTIEREN EINES HALBLEITERS UND KONTAKTANORDNUNG FÜR EINEN HALBLEITER

Title (fr)

PROCÉDÉ POUR METTRE EN CONTACT UN SEMI-CONDUCTEUR ET DISPOSITIF DE MISE EN CONTACT DESTINÉ À UN SEMI-CONDUCTEUR

Publication

EP 2783391 A1 20141001 (DE)

Application

EP 12797791 A 20121120

Priority

- DE 102011086687 A 20111121
- EP 2012073074 W 20121120

Abstract (en)

[origin: WO2013076064A1] The invention relates to a method for making contact with a semiconductor (10), and to a contact arrangement (1) for a semiconductor (10), wherein the semiconductor (10) is areally connected to a first contact partner (20) at at least one first area by the formation of a first soldering layer (30) having a predefined thickness. According to the invention, a polyimide layer (14) is applied as delimiting means on the semiconductor (10), said polyimide layer predefining the dimensions and/or the form of at least one soldering area (12) of the semiconductor (10).

IPC 8 full level

H01L 21/60 (2006.01); **H01L 23/48** (2006.01); **H01L 23/495** (2006.01)

CPC (source: CN EP US)

H01L 21/768 (2013.01 - US); **H01L 23/49838** (2013.01 - US); **H01L 24/27** (2013.01 - CN EP US); **H01L 24/32** (2013.01 - CN EP US); **H01L 24/33** (2013.01 - CN EP US); **H01L 24/36** (2013.01 - US); **H01L 24/37** (2013.01 - CN EP US); **H01L 24/40** (2013.01 - EP US); **H01L 23/49513** (2013.01 - CN EP US); **H01L 23/49524** (2013.01 - CN EP US); **H01L 24/29** (2013.01 - CN EP US); **H01L 24/84** (2013.01 - EP); **H01L 2224/26145** (2013.01 - CN EP US); **H01L 2224/27013** (2013.01 - CN EP US); **H01L 2224/29101** (2013.01 - CN EP US); **H01L 2224/32225** (2013.01 - CN EP US); **H01L 2224/32245** (2013.01 - CN EP US); **H01L 2224/33181** (2013.01 - CN EP US); **H01L 2224/352** (2013.01 - CN EP US); **H01L 2224/37011** (2013.01 - EP US); **H01L 2224/37012** (2013.01 - CN EP US); **H01L 2224/371** (2013.01 - CN EP US); **H01L 2224/4007** (2013.01 - EP US); **H01L 2224/40245** (2013.01 - EP US); **H01L 2224/49171** (2013.01 - CN EP US); **H01L 2224/83801** (2013.01 - EP US); **H01L 2224/84801** (2013.01 - EP US); **H01L 2924/00014** (2013.01 - EP); **H01L 2924/1305** (2013.01 - CN EP US); **H01L 2924/13055** (2013.01 - CN EP US); **H01L 2924/1306** (2013.01 - CN EP US); **H01L 2924/13091** (2013.01 - CN EP US)

C-Set (source: CN EP US)

CN

1. **H01L 2224/27013 + H01L 2924/07025**
2. **H01L 2224/29101 + H01L 2924/014**
3. **H01L 2224/371 + H01L 2924/00014**
4. **H01L 2924/1306 + H01L 2924/00**
5. **H01L 2924/1305 + H01L 2924/00**

EP

1. **H01L 2224/27013 + H01L 2924/07025**
2. **H01L 2224/29101 + H01L 2924/014**
3. **H01L 2224/371 + H01L 2924/00014**
4. **H01L 2924/1306 + H01L 2924/00**
5. **H01L 2924/1305 + H01L 2924/00**
6. **H01L 2224/84801 + H01L 2924/00014**
7. **H01L 2224/83801 + H01L 2924/00014**
8. **H01L 2924/00014 + H01L 2224/37099**
9. **H01L 2924/00014 + H01L 2224/73221**

US

1. **H01L 2224/27013 + H01L 2924/07025**
2. **H01L 2224/29101 + H01L 2924/014**
3. **H01L 2224/371 + H01L 2924/00014**
4. **H01L 2924/1306 + H01L 2924/00**
5. **H01L 2924/1305 + H01L 2924/00**
6. **H01L 2224/84801 + H01L 2924/00014**
7. **H01L 2224/83801 + H01L 2924/00014**

Citation (search report)

See references of WO 2013076064A1

Designated contracting state (EPC)

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DOCDB simple family (publication)

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DOCDB simple family (application)

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